3.3 V/5 V ECL Differential Receiver/Driver with High Gain

MC100EP16VA

Description

The EP16VA is a world-class differential receiver/driver. The device is functionally equivalent to the EP16 and LVEP16 devices but with high gain output. Q_{HG} and $\overline{Q_{HG}}$ outputs have a DC gain several times larger than the DC gain of an EP16.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μ F capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

Under open input conditions (pulled to $V_{EE})$ internal input clamps will force the Q_{HG} output LOW.

Special considerations are required for differential inputs under No Signal conditions to prevent instability.

The 100 Series contains temperature compensation.

Features

- 270 ps Typical Propagation Delay
- Gain = > 20
- 20 mV Minimum Input Voltage Swing
- Maximum Frequency = > 3 GHz Typical
- PECL Mode Operating Range: V_{CC} = 3.0 V to 5.5 Vwith V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = -3.0 V to -5.5 V
- Open Input Default State
- V_{BB} Output
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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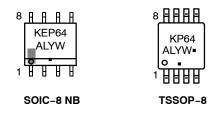
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D SUFFIX CASE 751-07

TSSOP-8 DT SUFFIX CASE 948R-02

MARKING DIAGRAMS*



K = MC100

Α

- = Assembly Location
- L = Wafer Lot
- ′ = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100EP16VADG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EP16VADTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EP16VADTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

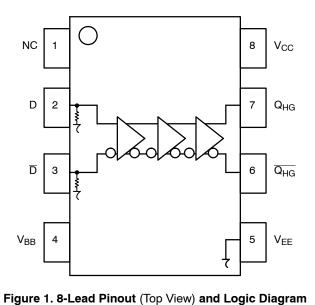


Table 1. PIN DESCRIPTION

PIN	FUNCTION
D*, <u>D</u> *	ECL Data Inputs
Q _{HG} , Q _{HG}	ECL High Gain Data Outputs
V _{BB}	Reference Voltage Output
V _{CC}	Positive Supply
V _{EE}	Negative Supply
NC	No Connect

* Pins will default LOW when left open.

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8	Level 1 Level 3
Flammability Rating Oxygen Index: 28 to 34	UL-94 V-0 @ 0.125 in
Transistor Count	167
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V_{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 -6	V
I _{out}	Output Current	Continuous Surge		50 100	mA
I _{BB}	V _{BB} Sink/Source			±0.5	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
T _{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1305	1430	1555	1305	1430	1555	1305	1430	1555	mV
VIH	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
VIL	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V_{BB}	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μA
۱ _{IL}	Input LOW Current	0.5			0.5			0.5			μA

Table 4. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to –2.2 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. VIHCMR min varies 1:1 with VEE, VIHCMR max varies 1:1 with VCC. The VIHCMR range is referenced to the most positive side of the differential input signal.

		−40°C			25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	
I _{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA	
V _{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV	
V _{OL}	Output LOW Voltage (Note 2)	3005	3180	3355	3005	3180	3355	3005	3180	3355	mV	
VIH	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV	
V _{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV	
V_{BB}	Output Voltage Reference	3475	3575	3675	3475	3575	3675	3475	3575	3675	mV	
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V	
I _{IH}	Input HIGH Current			150			150			150	μΑ	
١ _{IL}	Input LOW Current	0.5			0.5			0.5			μA	

Table 5. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to –0.5 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V. 3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

			–40°C 25°C					85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1995	-1870	-1745	-1995	-1870	-1745	-1995	-1870	-1745	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
V_{BB}	Output Voltage Reference	-1525	-1425	-1325	-1525	-1425	-1325	-1525	-1425	-1325	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V _{EE} +2.0		0.0	V _{EE}	+2.0	0.0	V _{EE}	+2.0	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} – 2.0 V.

V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. AC CHARACTERISTICS ($V_{CC} = 0 V$; $V_{EE} =$	-3.0 V to -5.5 V or V _{CC} = 3.0 V to 5.5 V; V _{EE} = 0 V (Note 1))
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		-40°C			25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	
f _{max}	Maximum Frequency (See Figure 2 F _{max} /JITTER)		> 3			> 3			> 3		GHz	
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential	200	260	320	220	270	340	250	320	390	ps	
t _{SKEW}	Duty Cycle Skew (Note 2)		5.0	20		5.0	20		5.0	20	ps	
^t JITTER	Cycle-to-Cycle Jitter (See Figure 2 F _{max} /JITTER)		0.2	< 1		0.2	< 1		0.2	< 1	ps	
V _{PP}	Input Voltage Swing (Differential Configuration) (See Figure 3)	20	800	1200	20	800	1200	20	800	1200	mV	
t _r t _f	Output Rise/Fall Times Q, Q (20% – 80%)	70	110	170	80	110	180	80	120	200	ps	

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC}–2.0 V.

2. Skew is measured between outputs under identical transitions. Duty cycle skew is defined only for differential operation when the delays are measured from the cross point of the inputs to the cross point of the outputs.

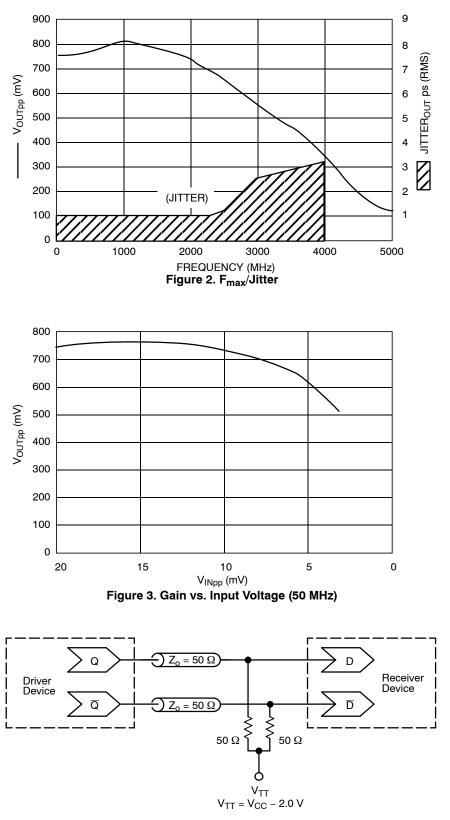


Figure 4. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices)

Resource Reference of Application Notes

- AN1405/D-ECL Clock Distribution TechniquesAN1406/D-Designing with PECL (ECL at +5.0 V)AN1503/D-ECLinPS™ I/O SPiCE Modeling KitAN1504/D-Metastability and the ECLinPS FamilyAN1568/D-Interfacing Between LVDS and ECLAN1672/D-The ECL Translator GuideAND8001/D-Odd Number Counters DesignAND8002/D-Marking and Date Codes
- AND8020/D Termination of ECL Logic Devices
- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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7.

8

COLLECTOR, #1

COLLECTOR, #1

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-T- SEATING

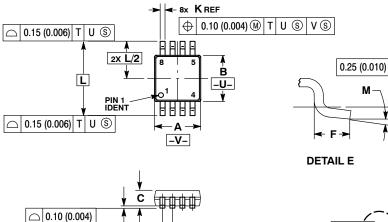
PLANE

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DATE 07 APR 2000



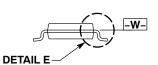
0.25 (0.010)

NOTES:

4.

5.

PER SIDE.



	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.114	0.122	
В	2.90	3.10	0.114	0.122	
С	0.80	1.10	0.031	0.043	
D	0.05	0.15	0.002	0.006	
F	0.40	0.70	0.016	0.028	
G	0.65	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016	
L	4.90 BSC		0.193 BSC		
М	0°	6 °	0 °	6 °	

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLED

FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010)

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